

Serial No.: 09/413,462

Docket No.: YOR919990358US1
(12906)

**ATTACHMENT: VERSION WITH MARKINGS SHOWING CHANGES MADE
IN THE CLAIMS:**

21. (Thrice Amended) A semiconductor structure comprising at least one metal silicate dielectric material that is in direct contact with a silicon oxide layer, said silicon oxide layer [being formed] is located directly on a Si-containing substrate, and an electrically conductive contact located directly on an upper horizontal surface of each of said metal silicate dielectric materials.

28. (Twice Amended) A field effect transistor comprising:
a Si-containing semiconductor substrate;
spaced apart source/drain regions in said substrate defining a channel region therein;
a dielectric layer located atop said channel region, said dielectric layer including a bottom SiO₂ layer and a top metal silicate layer; and
a gate electrode [formed over] located directly on an upper horizontal surface of said top metal silicate layer.

34. (Four Times Amended) A capacitor comprising a metal silicate dielectric material and a SiO₂ layer sandwiched between top and bottom electrode materials, wherein said [at least one] metal silicate dielectric material is located directly atop said SiO₂ layer and said top electrode is located directly on an upper horizontal surface of said metal silicate dielectric material.